



STY100NM60N

N-channel 600 V, 0.028 Ω typ., 98 A MDmesh™ II
Power MOSFET in a Max247 package

Datasheet — production data

Features

Type	V _{DSS} @ T _{Jmax}	R _{DS(on)} max	I _D
STY100NM60N	650 V	< 0.029 Ω	98 A

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

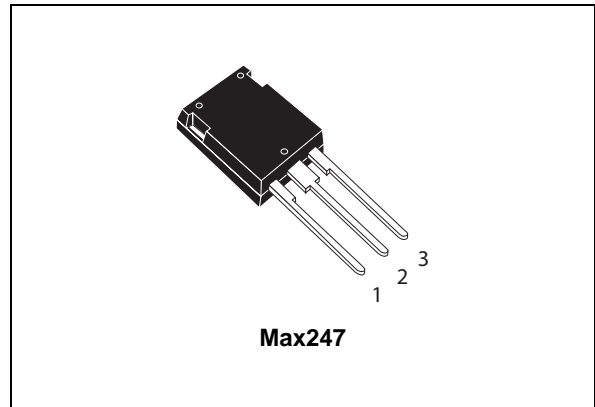


Figure 1. Internal schematic diagram

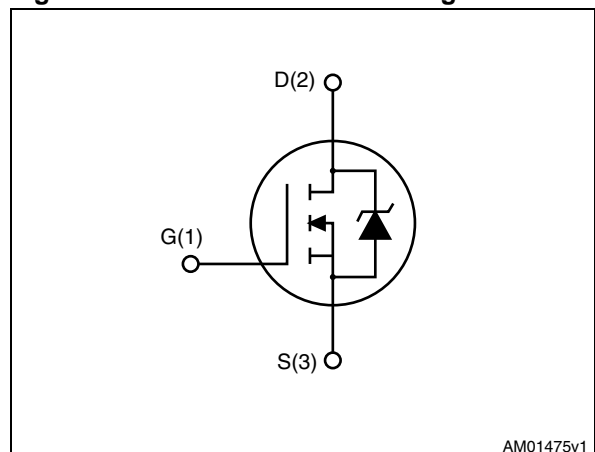


Table 1. Device summary

Order code	Marking	Package	Packaging
STY100NM60N	100NM60N	Max247	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate- source voltage	25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	98	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	62	A
$I_{DM}^{(1)}$	Drain current (pulsed)	392	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	625	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
T_{stg}	Storage temperature	- 55 to 150	$^\circ\text{C}$
T_j	Max. operating junction temperature		$^\circ\text{C}$

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 98\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS\text{ peak}} \leq V_{(BR)DSS}$, $V_{DD} = 80\% V_{(BR)DSS}$.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.2	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	30	$^\circ\text{C}/\text{W}$
T_j	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	15	A
E_{AS}	Single pulse avalanche energy (starting $T_j=25\text{ }^\circ\text{C}$, $I_D=I_{ar}$, $V_{DD}=50$)	757	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified).

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 1\text{ mA}$	600			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 600\text{ V}$ $V_{DS} = 600\text{ V}, T_C = 125\text{ °C}$			10 150	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 25\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 49\text{ A}$		0.028	0.029	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 50\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0$	-	9600	-	pF
C_{oss}	Output capacitance			850		pF
C_{rss}	Reverse transfer capacitance			50		pF
$C_{oss(eq)}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }480\text{ V}, V_{GS} = 0$	-	1602	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	1.3	-	Ω
Q_g	Total gate charge	$V_{DD} = 480\text{ V}, I_D = 98\text{ A},$ $V_{GS} = 10\text{ V}$ (see Figure 15)	-	330	-	nC
Q_{gs}	Gate-source charge			40		nC
Q_{gd}	Gate-drain charge			174		nC

1. $C_{oss(eq)}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}, I_D = 49\text{ A},$ $R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$ (see Figure 16) and (see Figure 19)	-	45	-	ns
t_r	Rise time			52		ns
$t_{d(off)}$	Turn-off delay time			372		ns
t_f	Fall time			81		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		98	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		392	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 98 \text{ A}, V_{GS} = 0$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 98 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$	-	622		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 60 \text{ V}$	-	16.5		μC
I_{RRM}	Reverse recovery current	(see Figure 16)	-	52.5		A
t_{rr}	Reverse recovery time	$I_{SD} = 98 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$	-	820		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 60 \text{ V}, T_j = 150 \text{ }^\circ\text{C}$	-	27		μC
I_{RRM}	Reverse recovery current	(see Figure 16)	-	66		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

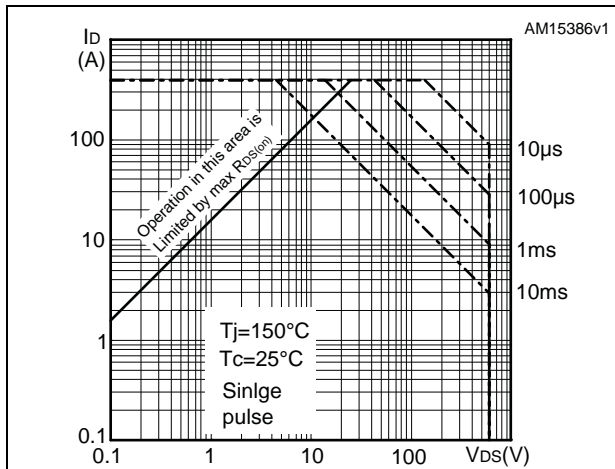


Figure 3. Thermal impedance

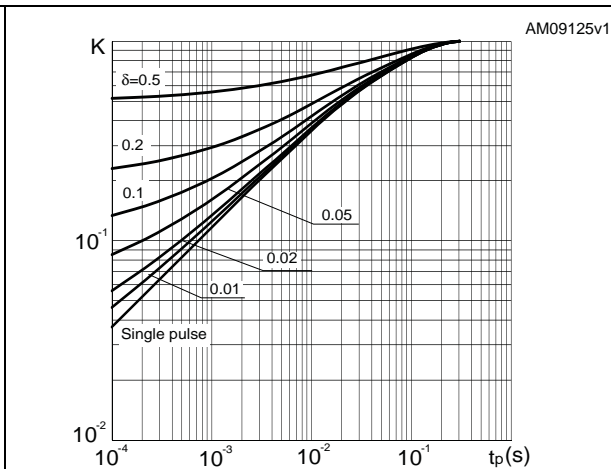


Figure 4. Output characteristics

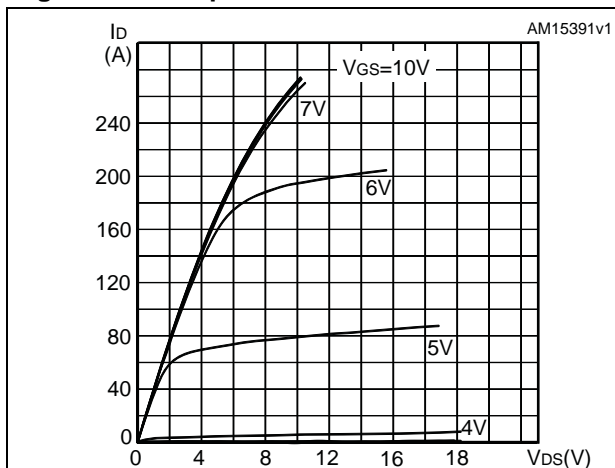


Figure 5. Transfer characteristics

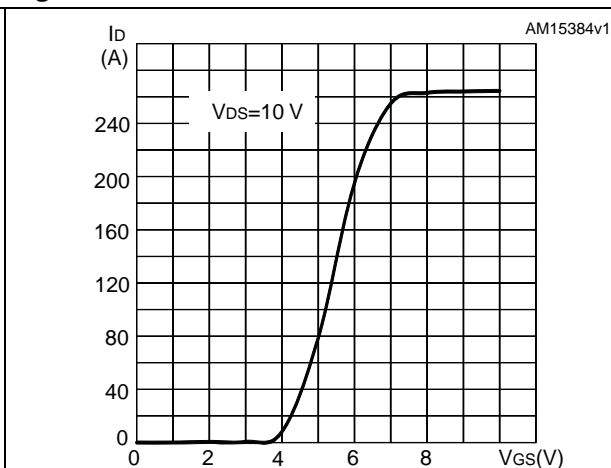


Figure 6. Gate charge vs gate-source voltage

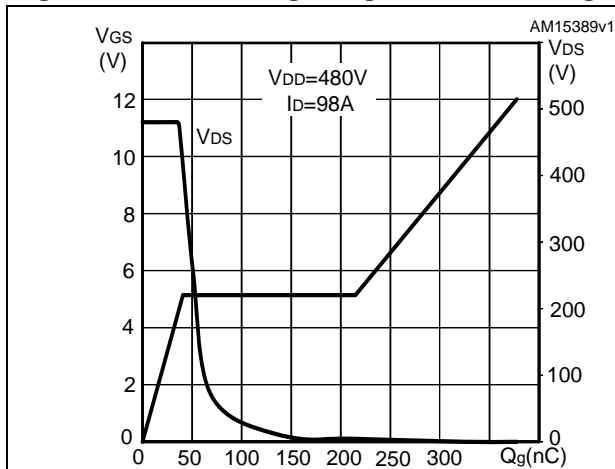


Figure 7. Static drain-source on-resistance

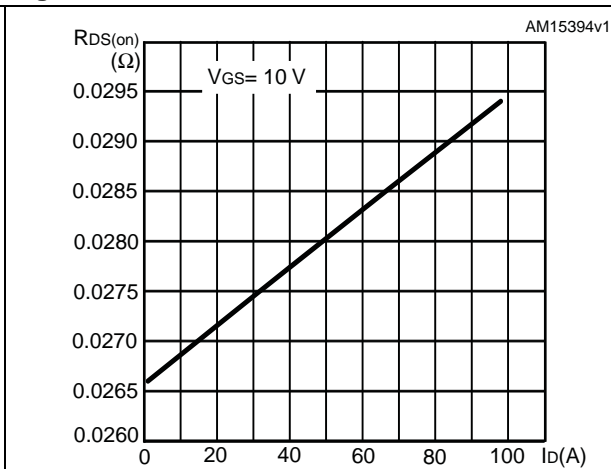


Figure 8. Capacitance variations

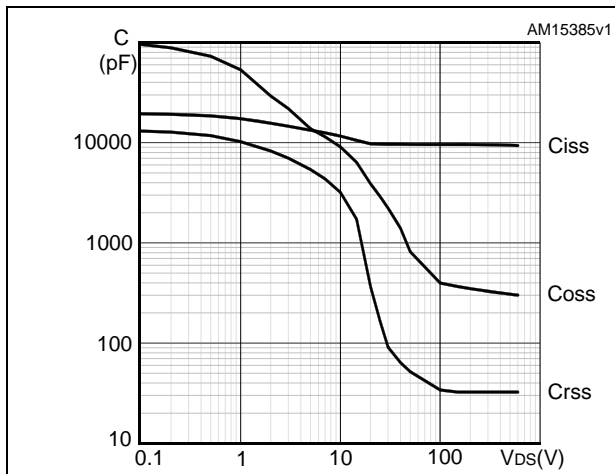


Figure 9. Normalized on-resistance vs temperature

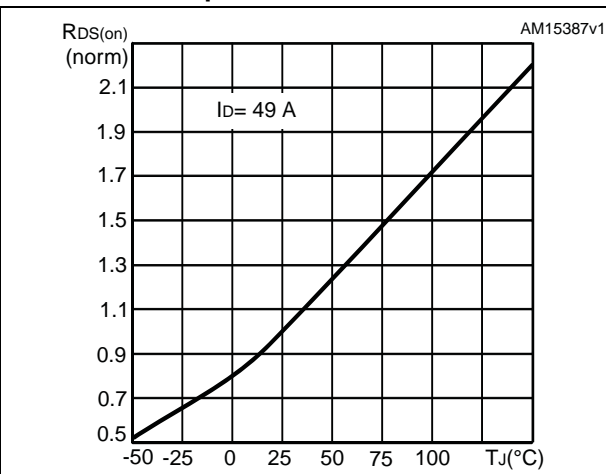


Figure 10. Normalized gate threshold voltage vs temperature

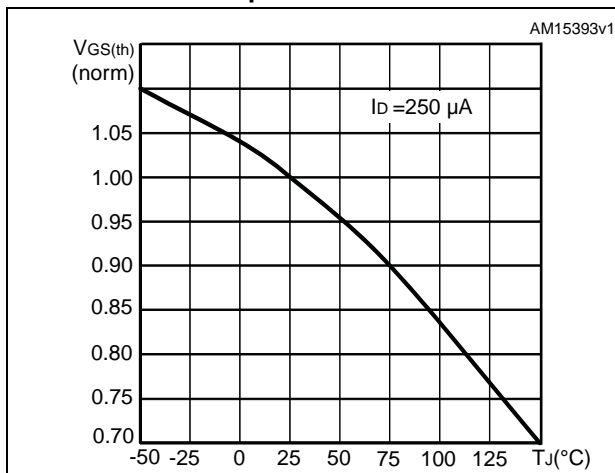


Figure 11. Normalized B_{VDS} vs temperature

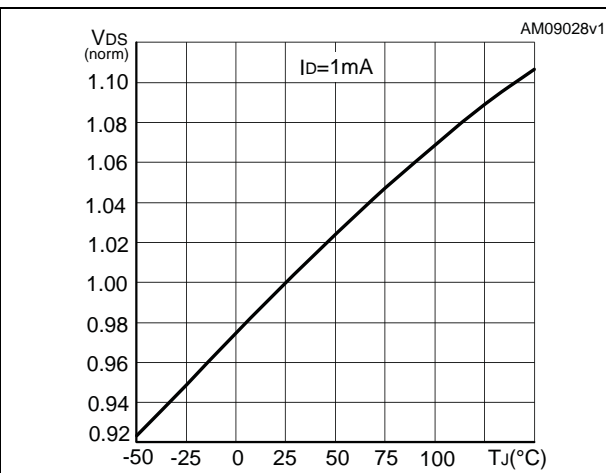


Figure 12. Source-drain diode forward characteristics

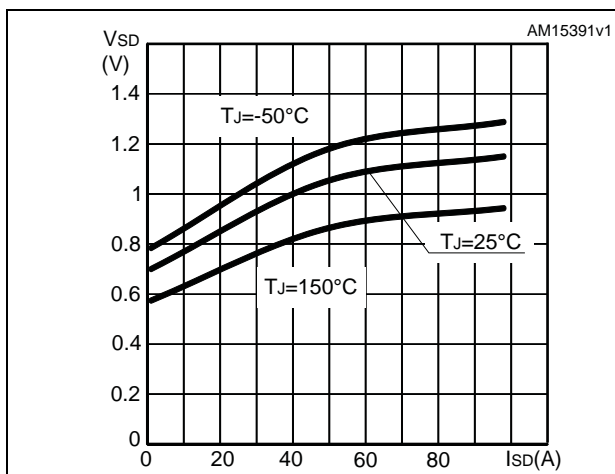
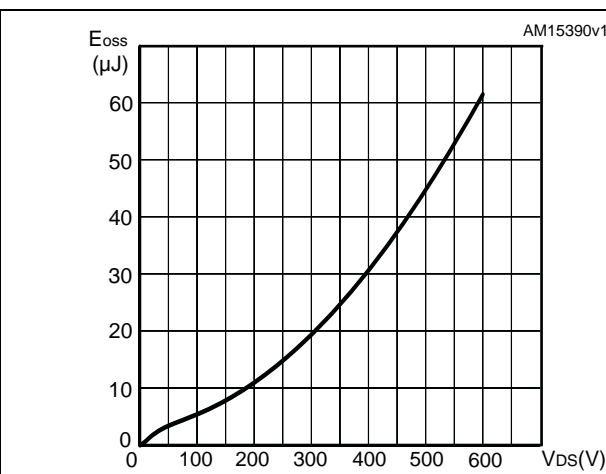
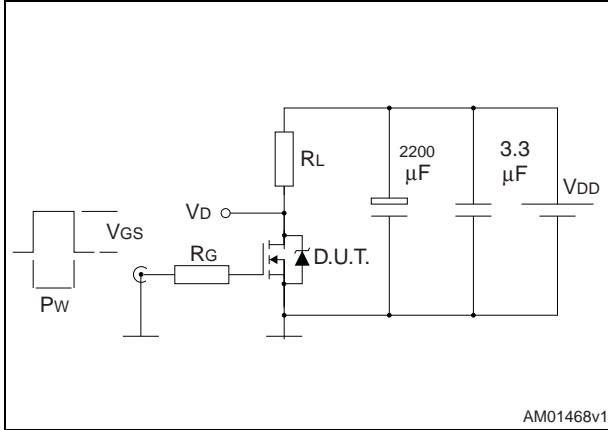


Figure 13. Output capacitance stored energy



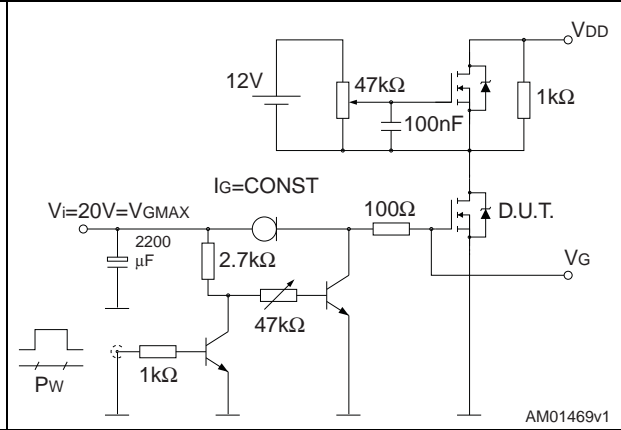
3 Test circuits

Figure 14. Switching times test circuit for resistive load



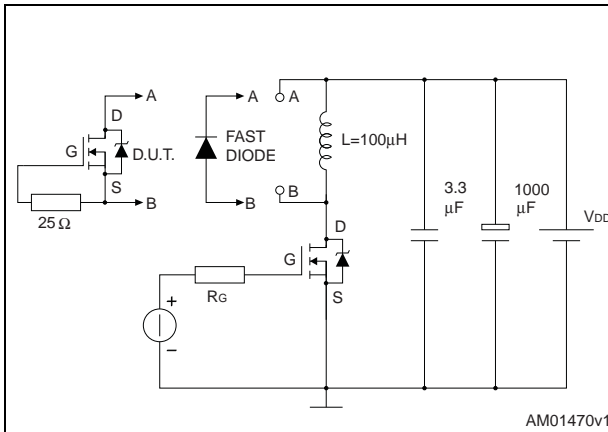
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Figure 15. Gate charge test circuit



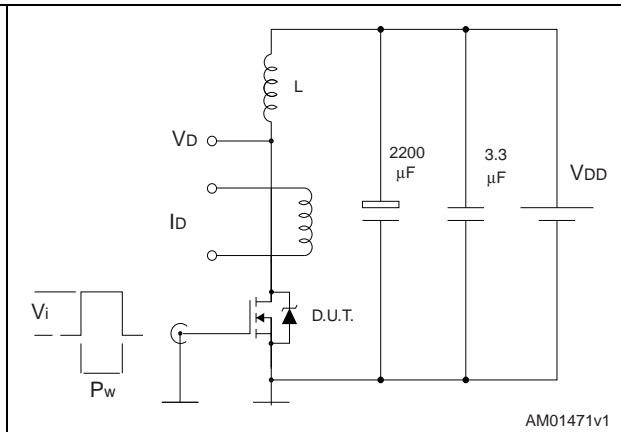
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Figure 16. Test circuit for inductive load switching and diode recovery times



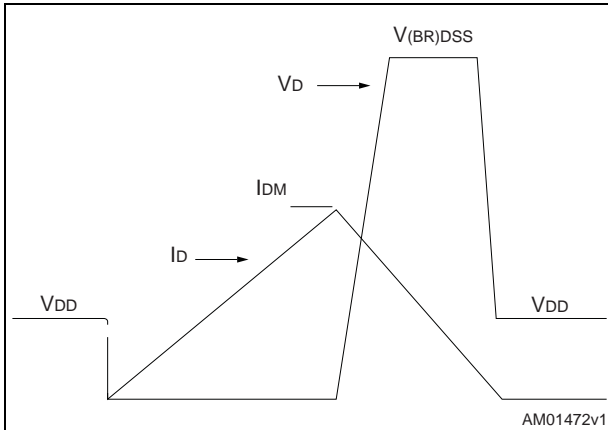
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Figure 17. Unclamped inductive load test circuit



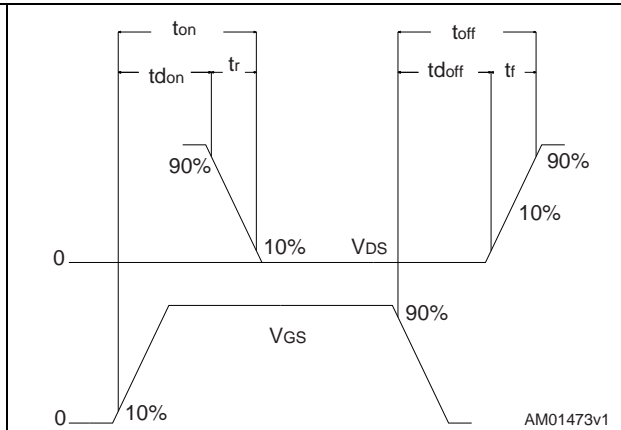
AM01471v1

Figure 18. Unclamped inductive waveform



AM01472v1

Figure 19. Switching time waveform



AM01473v1

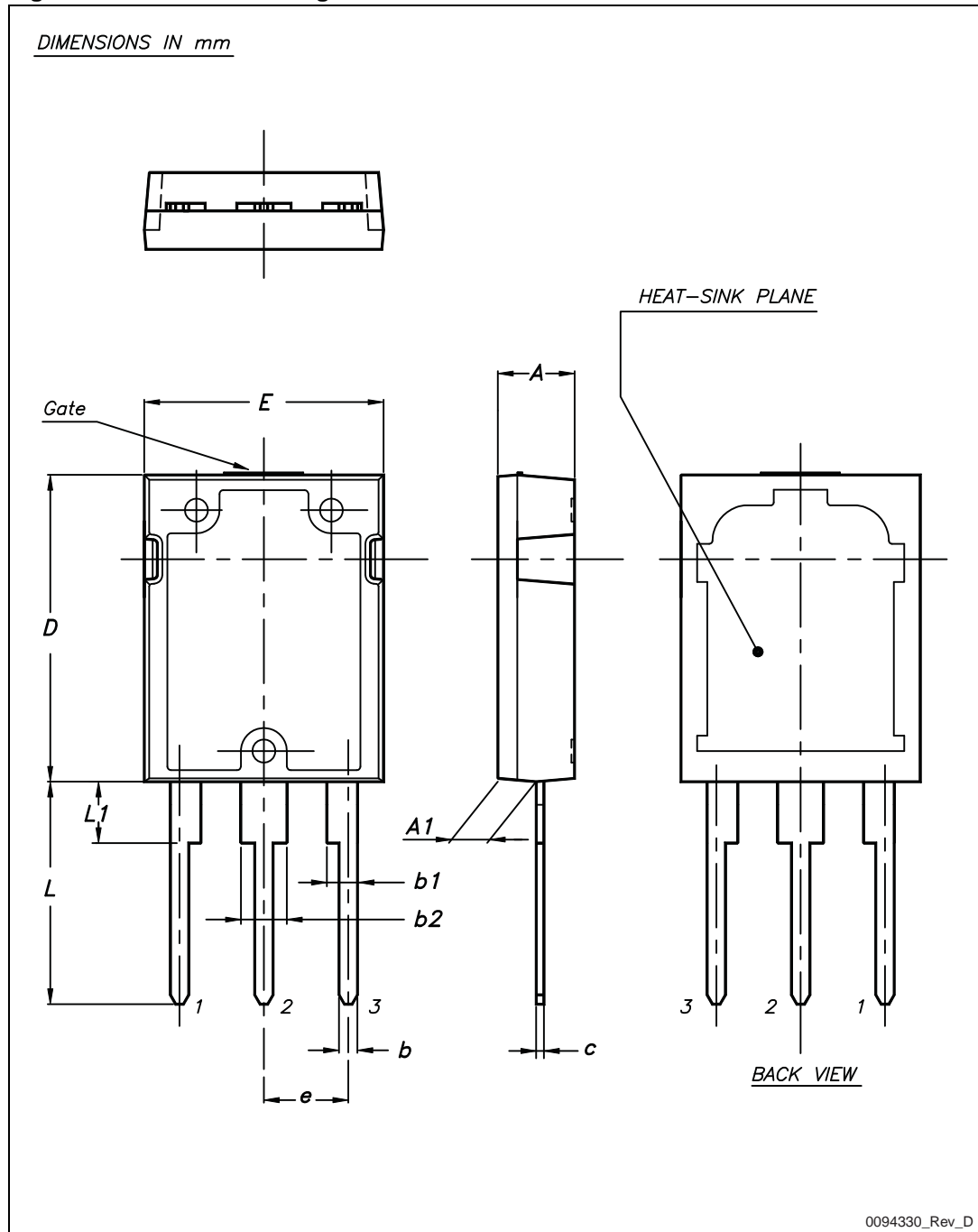
4 Package mechanical data

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Table 9. Max247 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.70		5.30
A1	2.20		2.60
b	1.00		1.40
b1	2.00		2.40
b2	3.00		3.40
c	0.40		0.80
D	19.70		20.30
e	5.35		5.55
E	15.30		15.90
L	14.20		15.20
L1	3.70		4.30

Figure 20. Max247 drawing



5 Revision history

Table 10. Document revision history

Date	Revision	Changes
14-Sep-2011	1	First release.
05-Nov-2012	2	Document status promoted from preliminary to production data. Added Section 2.1: Electrical characteristics (curves) . Minor text changes.

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